V V Romaka

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

81	780	12	24
papers	citations	h-index	g-index
115	879 ext. citations	3.3	3.89
ext. papers		avg, IF	L-index

#	Paper	IF	Citations
81	On the constitution and structural characterization of the ternary system Sm-Ni-Sn. <i>Journal of Solid State Chemistry</i> , 2022 , 123213	3.3	
80	Physical properties of {Ti,Zr,Hf}NiSn compounds Dalton Transactions, 2021, 51, 361-374	4.3	
79	Mechanism of Defect Formation in Zr1 IkVxNiSn Thermoelectric Material. <i>Ukrainian Journal of Physics</i> , 2021 , 66, 333	0.4	
78	Experimental and theoretical investigation of the YNIBb and TmNIBb systems. <i>Journal of Alloys and Compounds</i> , 2021 , 855, 157334	5.7	2
77	Structure and properties of MgB2 bulks: ab-initio simulations compared to experiment. <i>IOP Conference Series: Materials Science and Engineering</i> , 2020 , 756, 012020	0.4	2
76	Crystal structure and magnetic properties of TmV0.17Ge2 and LuV0.15Ge2 ternary germanides. Journal of Physics and Chemistry of Solids, 2020, 137, 109205	3.9	1
75	Determination of structural disorder in Heusler-type phases. <i>Computational Materials Science</i> , 2020 , 172, 109307	3.2	8
74	High-ZT half-Heusler thermoelectrics, Ti0.5Zr0.5NiSn and Ti0.5Zr0.5NiSn0.98Sb0.02: Physical properties at low temperatures. <i>Acta Materialia</i> , 2019 , 166, 466-483	8.4	23
73	Thermoelectric Half-Heusler compounds TaFeSb and Ta1-xTixFeSb (0 lk ld.11): Formation and physical properties. <i>Intermetallics</i> , 2019 , 111, 106468	3.5	5
72	MgB2 Wires and Bulks With High Superconducting Performance. <i>IEEE Transactions on Applied Superconductivity</i> , 2019 , 29, 1-5	1.8	3
71	Manufacturing, Structure, Properties of MgB2-Based Materials. <i>Journal of Superconductivity and Novel Magnetism</i> , 2019 , 32, 3115-3120	1.5	
70	Synthesis, electrical transport, magnetic properties and electronic structure of Ti1-Sc CoSb semiconducting solid solution. <i>Journal of Alloys and Compounds</i> , 2019 , 805, 840-846	5.7	1
69	Correlations Between Superconducting Characteristics and Structure of MgB2-Based Materials, ab-Initio Modeling. <i>IEEE Transactions on Applied Superconductivity</i> , 2019 , 29, 1-7	1.8	1
68	Structure and Properties of MgB2: Effect of Ti-O and TiC Additions. <i>IEEE Transactions on Applied Superconductivity</i> , 2018 , 28, 1-5	1.8	3
67	On the constitution and thermodynamic modelling of the system Zr-Ni-Sn. <i>Journal of Alloys and Compounds</i> , 2018 , 742, 1058-1082	5.7	17
66	Experimental and DFT study of the VIIoBb ternary system. <i>Journal of Alloys and Compounds</i> , 2018 , 739, 771-779	5.7	5
65	Preparation and Properties of MgB2 Thin Films. <i>IEEE Transactions on Applied Superconductivity</i> , 2018 , 28, 1-7	1.8	1

(2014-2018)

64	The half Heusler system TiFeSb-TiCoSb with Sb/Sn substitution: phase relations, crystal structures and thermoelectric properties. <i>Dalton Transactions</i> , 2018 , 47, 879-897	4.3	26
63	Crystallographic, magnetic and electrical characteristics of R3Ni8Sn4 compounds (R = Y, Nd, Sm, Gd, and Tb). <i>Journal of Alloys and Compounds</i> , 2017 , 701, 358-365	5.7	2
62	Features of the band structure and conduction mechanisms of n-HfNiSn heavily doped with Y. <i>Semiconductors</i> , 2017 , 51, 139-145	0.7	1
61	(V,Nb)-doped half Heusler alloys based on {Ti,Zr,Hf}NiSn with high ZT. <i>Acta Materialia</i> , 2017 , 131, 336-34	18.4	97
60	Structure and Properties of MgB2 Bulks, Thin Films, and Wires. <i>IEEE Transactions on Applied Superconductivity</i> , 2017 , 27, 1-5	1.8	8
59	Prediction of the Thermoelectric Properties of Half-Heusler Phases from the Density Functional Theory 2017 , 286-323		1
58	Thermoelectric high ZT half-Heusler alloys Ti1网ZrxHfyNiSn (0欧面; 0欧面). <i>Acta Materialia</i> , 2016 , 104, 210-222	8.4	143
57	Peculiarities of thermoelectric half-Heusler phase formation in Gd-Ni-Sb and Lu-Ni-Sb ternary systems. <i>Journal of Solid State Chemistry</i> , 2016 , 239, 145-152	3.3	17
56	Features of conductivity mechanisms in heavily doped compensated V1⊠ Ti x FeSb Semiconductor. <i>Semiconductors</i> , 2016 , 50, 860-868	0.7	4
55	Phase relationships in the {Ho, Er}NiBn ternary systems at 673K and crystal structure of new ternary compounds. <i>Journal of Alloys and Compounds</i> , 2015 , 631, 288-297	5.7	3
54	Features of the band structure and conduction mechanisms of n-HfNiSn semiconductor heavily Lu-doped. <i>Semiconductors</i> , 2015 , 49, 290-297	0.7	4
53	Structural defect generation and band-structure features in the HfNi1 Ix Co x Sn semiconductor. <i>Semiconductors</i> , 2015 , 49, 985-991	0.7	1
52	On the constitution and thermodynamic modelling of the system TiNiBn. RSC Advances, 2015, 5, 92270-9	9 3.7 91	37
51	The Sr-poor part of the Sr[Pd,Pt][Si,Ge] systems: Phase equilibria and crystal structure of ternary phases. <i>Journal of Alloys and Compounds</i> , 2015 , 618, 656-665	5.7	2
50	Peculiarities of thermoelectric half-Heusler phase formation in ZrtoBb ternary system. <i>Journal of Alloys and Compounds</i> , 2014 , 585, 448-454	5.7	20
49	The ViuBb ternary system at 773K: Crystal, band structure, and physical properties. <i>Journal of Alloys and Compounds</i> , 2014 , 589, 200-206	5.7	6
48	Peculiarity of component interaction in ZrMn[Sn, Sb] ternary systems. <i>Journal of Alloys and Compounds</i> , 2014 , 611, 401-409	5.7	6
47	Features of the band structure and conduction mechanisms in the n-HfNiSn semiconductor heavily doped with Ru. <i>Semiconductors</i> , 2014 , 48, 1545-1551	0.7	2

46	The system BallnBn at 500 LC: Phase equilibria, crystal and electronic structure of ternary phases. Journal of Alloys and Compounds, 2014 , 585, 287-298	5.7	8
45	Formation and stability of the clathrate-I structure in the systems Sr[Ni,Cu,Zn)	3.5	4
44	Contribution to the investigation of the YūuBn ternary system. <i>Chemistry of Metals and Alloys</i> , 2014 , 7, 132-138	1	2
43	Effect of the accumulation of excess Ni atoms in the crystal structure of the intermetallic semiconductor n-ZrNiSn. <i>Semiconductors</i> , 2013 , 47, 892-898	0.7	12
42	Features of conduction mechanisms in n-HfNiSn semiconductor heavily doped with a Rh acceptor impurity. <i>Semiconductors</i> , 2013 , 47, 1145-1152	0.7	4
41	Novel refractory phase, Ta7Si2(Si(x)B(1-x))2. <i>Inorganic Chemistry</i> , 2013 , 52, 11295-301	5.1	О
40	Peculiarities of structural disorder in Zr- and Hf-containing Heusler and half-Heusler stannides. <i>Intermetallics</i> , 2013 , 35, 45-52	3.5	39
39	Phase equilibria, formation, crystal and electronic structure of ternary compounds in TiNiBn and TiNiBb ternary systems. <i>Journal of Solid State Chemistry</i> , 2013 , 197, 103-112	3.3	46
38	Structural, magnetic and electronic transport studies of RAgSn2 compounds (R = Y, Tb, Dy, Ho and Er) with Cu3Au-type. <i>Bulletin of Materials Science</i> , 2013 , 36, 1247-1253	1.7	4
37	The systems SrZn[Si,Ge]: Phase equilibria and crystal structure of ternary phases. <i>Journal of Solid State Chemistry</i> , 2012 , 186, 87-93	3.3	5
36	Features of conductivity of the intermetallic semiconductor n-ZrNiSn heavily doped with a Bi donor impurity. <i>Semiconductors</i> , 2012 , 46, 887-893	0.7	5
35	Interaction of the components in YNiBn ternary system at 770 K and 670 K. <i>Intermetallics</i> , 2012 , 29, 116-122	3.5	6
34	Features of the conduction mechanisms of the n-HfNiSn semiconductor heavily doped with the Co acceptor impurity. <i>Semiconductors</i> , 2012 , 46, 1106-1113	0.7	5
33	Interaction of Vanadium with Iron and Antimony at 870 and 1070 K. European Journal of Inorganic Chemistry, 2012 , 2012, 2588-2595	2.3	11
32	Contribution to the investigation of ternary LuNiBn system. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 4530-4533	5.7	8
31	Crystal structure peculiarity and magnetic behavior of R2Cu4\(\mathbb{R}\)Sn5+x (R=Gd, Tb, and Dy) compounds. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 5206-5210	5.7	O
30	Peculiarity of component interaction in {Y, Dy}MnBn ternary systems. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 7559-7564	5.7	3
29	Peculiarities of component interaction in {Gd, Er}\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	5.7	2

(2008-2011)

28	Structural and thermoelectric properties of Zr1 Ik Er x NiSn solid solutions. <i>Inorganic Materials</i> , 2011 , 47, 637-644	0.9	2	
27	Features of a priori heavy doping of the n-TiNiSn intermetallic semiconductor. <i>Semiconductors</i> , 2011 , 45, 850-856	0.7	13	
26	Interaction between the components in the {Zr, Hf}-Ag-Sn ternary systems. <i>Chemistry of Metals and Alloys</i> , 2011 , 4, 234-242	1	2	
25	LuNi5Sn: A first representative of RNi5Sn stannides with CeCu5Au structure. <i>Journal of Alloys and Compounds</i> , 2010 , 493, L12-L14	5.7	7	
24	Crystallographic, magnetic and electrical characteristics of some R5\(\mathbb{N}\) intermetallics. Journal of Alloys and Compounds, 2010 , 493, 35-40	5.7	4	
23	Pd5Sn7A novel binary stannide in PdBn system. <i>Journal of Alloys and Compounds</i> , 2010 , 496, L7-L9	5.7	5	
22	Interaction of the components in the GdNiBn ternary system at 770K. <i>Journal of Alloys and Compounds</i> , 2010 , 505, 70-75	5.7	10	
21	Peculiarity of component interaction in Erfleßn ternary system at 670K and 770K. <i>Journal of Alloys and Compounds</i> , 2010 , 507, 67-71	5.7	5	
20	Features of an intermetallic n-ZrNiSn semiconductor heavily doped with atoms of rare-earth metals. <i>Semiconductors</i> , 2010 , 44, 293-302	0.7	13	
19	Crystal, electronic structure and electronic transport properties of the Ti1型VxNiSn (目0 D .10) solid solutions. <i>Journal of Solid State Chemistry</i> , 2010 , 183, 3023-3028	3.3	9	
18	Features of the structural, electrokinetic, and magnetic properties of the heavily doped ZrNiSn semiconductor: Dy acceptor impurity. <i>Semiconductors</i> , 2009 , 43, 7-13	0.7	3	
17	Interaction of the components in DyNiBn ternary system and crystal structure of new compounds. <i>Journal of Alloys and Compounds</i> , 2009 , 485, 275-279	5.7	9	
16	Peculiarity of component interaction in the Gd-Cu-Sn ternary system at 670 and 770 K. <i>Chemistry of Metals and Alloys</i> , 2009 , 2, 68-74	1	3	
15	Crystal structure and magnetic properties of Dy4Ni12Sn25 compound. <i>Journal of Alloys and Compounds</i> , 2008 , 453, L8-L10	5.7	5	
14	Magnetic properties of RNi3Sn2 compounds (R=Y, Sm, Gd, Tb, Dy). <i>Journal of Alloys and Compounds</i> , 2008 , 454, 5-9	5.7	3	
13	Phase equilibria in NdNiBn ternary system. <i>Journal of Alloys and Compounds</i> , 2008 , 454, 136-141	5.7	8	
12	Crystal structure of new RAgSn2 ternary compounds (R=Y, Gd, Tb, Dy, Ho, Er). <i>Journal of Alloys and Compounds</i> , 2008 , 457, 329-331	5.7	7	
11	Electric transport properties of RNi3Sn2 compounds (R=Y, Sm, Gd, Tb, Dy) and electronic structure of YNi3Sn2 and GdNi3Sn2. <i>Journal of Alloys and Compounds</i> , 2008 , 459, 8-12	5.7	6	

10	Crystal structure of new ternary RE1.9Cu9.2Sn2.8 compounds (RE = Y, Ce, Pr, Nd, Sm, Gd, Tb, Dy, Ho, Er, Tm, Yb, and Lu). <i>Journal of Alloys and Compounds</i> , 2008 , 460, 283-288	5.7	3
9	Interaction between components in HftuBb ternary system at 770K. <i>Journal of Alloys and Compounds</i> , 2008 , 461, 147-149	5.7	3
8	Zr(3)NiSb(7): a new anti-mony-enriched ZrSb(2) derivative. <i>Acta Crystallographica Section E: Structure Reports Online</i> , 2008 , 64, i47		
7	Dy2Ni7Sn3: a new member of the CaCu5 family of intermetallics. <i>Acta Crystallographica Section C: Crystal Structure Communications</i> , 2008 , 64, i45-6		5
6	Mechanism of local amorphization of a heavily doped Ti1 \times V x CoSb intermetallic semiconductor. Semiconductors, 2008 , 42, 753-760	0.7	4
5	Electrical transport properties and electronic structure of RNiSn compounds (R = Y, Gd, Tb, Dy, and Lu). <i>Chemistry of Metals and Alloys</i> , 2008 , 1, 298-302	1	4
4	Features of electrical conductivity in the n-ZrNiSn intermetallic semiconductor heavily doped with the In acceptor impurity. <i>Semiconductors</i> , 2007 , 41, 1041-1047	0.7	7
3	Interaction of the components in the DyAgBn ternary system at 870K. <i>Journal of Alloys and Compounds</i> , 2007 , 439, 128-131	5.7	10
2	Crystal structure of the ternary R3Ag4Sn4 stannides (R=Y, Gd, Tb, Dy, Ho) with Gd3Cu4Ge4-type structure. <i>Journal of Alloys and Compounds</i> , 2007 , 443, 68-70	5.7	6
1	Phase equilibria in the DylluBn ternary system. <i>Journal of Alloys and Compounds</i> , 2005 , 395, 113-116	5.7	8